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# N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
100	$0.095 \text{ at V}_{GS} = 10 \text{ V}$	15		
	0.100 at V <sub>GS</sub> = 6 V	15		

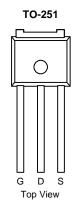
#### **FEATURES**

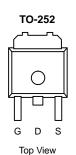
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested

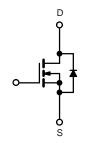


#### **APPLICATIONS**

· Primary Side Switch







N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	100	V		
Gate-Source Voltage		$V_{GS}$	± 20	V		
Continuous Dunin Comment /T 475 °C\b	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	15			
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 125 °C		8.7			
Pulsed Drain Current		I <sub>DM</sub>	45	А		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	15			
Avalanche Current		I <sub>AR</sub>	15			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	11.3	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	62 <sup>b</sup>	- W		
	T <sub>A</sub> = 25 °C	' Б	2.7 <sup>a</sup>			
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	16	20	°C/W
Junction-to-Ambient*	Steady State		45	55	
Junction-to-Case		R <sub>thJC</sub>	2	2.4	

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



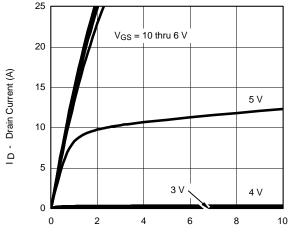
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static					<u>l</u>		
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V, } I_D = 250  \mu\text{A}$	100			- V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	50 μA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50		
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	15			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.095	0.110		
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C			0.190		
Drain-Source On-State Resistance <sup>D</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C			0.250	Ω	
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 10 A		0.100	0.115		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		25		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			900		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115			
Reverse Transfer Capacitance	C <sub>rss</sub>			70			
Total Gate Charge <sup>c</sup>	$Q_g$			20	25		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		5.5		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7			
Gate Resistance	R <sub>g</sub>		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 75 V, $R_L$ = 5 $\Omega$ $I_D \cong$ 15 A, $V_{GEN}$ = 10 V, $R_G$ = 2.5 $\Omega$		35	55	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			17	25		
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	<sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				45	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15 A, dl/dt = 100 A/μs		55	85	ns	

#### Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

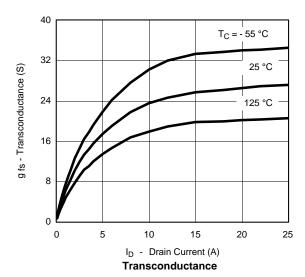
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

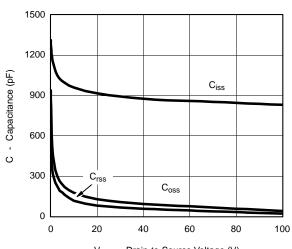
### TYPICAL CHARACTERISTICS (25 °C unless noted)



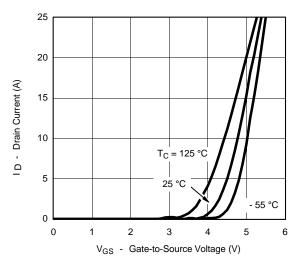
 $V_{DS}\,$  - Drain-to-Source Voltage (V)

#### **Output Characteristics**

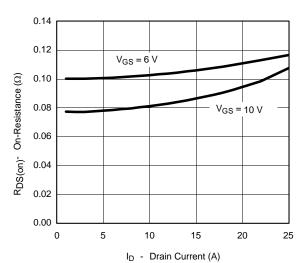




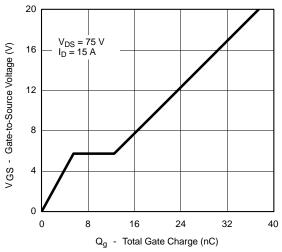
 $V_{DS}\,$  - Drain-to-Source Voltage (V) Capacitance



**Transfer Characteristics** 



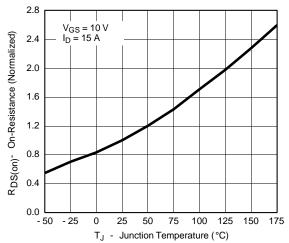
On-Resistance vs. Drain Current



**Gate Charge** 

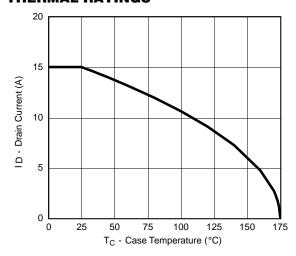
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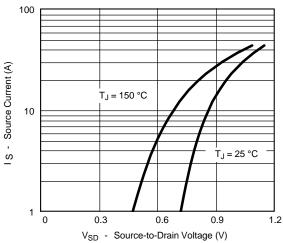


On-Resistance vs. Junction Temperature

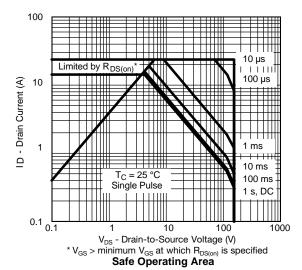
## THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



Normalized Thermal Transient Impedance, Junction-to-Case

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